



FINAL PRODUCT/PROCESS CHANGE NOTIFICATION # 16790FM

Generic Copy

Issue Date: 25-Sep-2014

TITLE: Final PCN for wafer fab transfer from Gunma and Gifu in Japan to ON Semiconductor Niigata Co., Ltd. in Niigata, Japan (Group FM).

PROPOSED FIRST SHIP DATE: starting on 1-Jan-2015 (the actual ship date will be different by each product, please check with the responsible Sales person).

AFFECTED CHANGE CATEGORY(S): Wafer Fabrication Location Change

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or Yasuhiro.Igarashi@onsemi.com

SAMPLES: Contact your local ON Semiconductor Sales Office or Shigehito.Matsumoto@onsemi.com

ADDITIONAL RELIABILITY DATA: May be available

Contact your local ON Semiconductor Sales Office or Kazutoshi.Kitazume@onsemi.com

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact [<quality@onsemi.com>](mailto:quality@onsemi.com)

DESCRIPTION AND PURPOSE:

This is a Final Process Change Notification to announce the transfer of products from ON Semiconductor wafer fabrication sites located in Gunma and Gifu to ON Semiconductor Niigata Co., Ltd. (OSNC). OSNC is located in Niigata, Japan.

The product design and electrical specifications will remain identical. A full electrical characterization over the temperature range will be performed for each product to check the device functionality and electrical specifications. Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.



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RELIABILITY DATA SUMMARY

Group FM

| Test: | Conditions: | Interval: | Results |
|---|---|------------|---------|
| Steady State Operating Life (This test isn't performed for diodes) | Tj=150degC | 1000 hrs | Pass |
| High Temperature Reverse Bias | Ta=150/125degC, VDSS/VR=max | 1000 hrs | Pass |
| Temp Humidity Storage | Ta=85degC, RH=85% | 1000 hrs | Pass |
| Temperature Cycle | Ta=-55degC to 150/125degC 30min | 100 cycles | Pass |
| Pressure Cooker | Ta=121degC, 2.03 × 10 ⁵ Pa, 100% | 50 hrs | Pass |
| High Temperature Storage | Ta=150/125degC | 1000 hrs | Pass |
| Low Temperature Storage | Ta=-55degC | 1000 hrs | Pass |
| Resistance to Soldering heat(Reflow) | Solder Temp.: 260degC ± 5degC | 10s | Pass |
| Solderability | Solder Temp.: 245degC ± 5degC | 5s | Pass |

Notice) Temperature description: 150/125degC means FET/DIODE

ELECTRICAL CHARACTERISTIC SUMMARY

There is no change in electrical parametric performance. Characterization data is available upon request.

CHANGED PART IDENTIFICATION

No change to current part marking will occur. Marking traceability codes will be able to identify wafer fab die source.

List of affected parts:

Group FM

| PART_ID |
|--------------|
| 1SV251-TB-E |
| 2SK536-TB-E |
| SVC203C-TB-E |
| SVC230-TB-E |
| SVC276-TL-E |
| SVC710-TL-E |